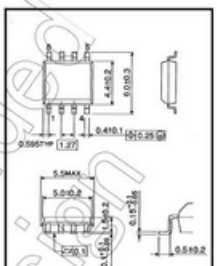
TPC8026

Lithium Ion Battery Applications
Portable Equipment Applications
Notebook PC Applications

- Small footprint due to small and thin package
- Low drain-source ON resistance: $R_{DS\ (ON)}$ = 5.1 mΩ (typ.)
- High forward transfer admittance: $|Y_{fs}|$ = 30 S (typ.)
- Low leakage current: I_{DSS} = 10 μA (max) (V_{DS} = 30 V)
- Enhancement mode: V_{th} = 1.3 to 2.5 V (V_{DS} = 10 V, I_D = 1 mA)

Unit: mm

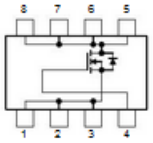


1, 2, 3	SOURCE
4	GATE
5, 6, 7, 8	DRAIN

JEDEC	—
JEITA	—
TOSHIBA	2-6J1B

Weight: 0.08 g (typ.)

Circuit Configuration



Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	30	V
Drain-gate voltage (R_{GS} = 20 kΩ)		V_{DGR}	30	V
Gate-source voltage		V_{GSS}	±20	V
Drain current	DC (Note 1)	I_D	13	A
	Pulse (Note 1)	I_{DP}	52	
Drain power dissipation (t = 10 s) (Note 2a)		P_D	1.9	W
Drain power dissipation (t = 10 s) (Note 2b)		P_D	1.0	W
Single pulse avalanche energy (Note 3)		E_{AS}	44	mJ
Avalanche current		I_{AR}	13	A
Repetitive avalanche energy (Note 2a) (Note 4)		E_{AR}	0.048	mJ
Channel temperature		T_{ch}	150	°C
Storage temperature range		T_{stg}	−55 to 150	°C

Note 1, Note 2, Note 3 and Note 4: See the next page.

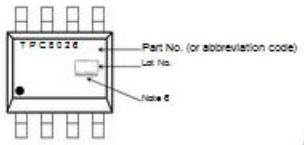
Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

This transistor is an electrostatic-sensitive device. Please handle with caution.

Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to ambient (t = 10 s) (Note 2a)	$R_{th\ (ch-a)}$	65.8	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2b)	$R_{th\ (ch-a)}$	125	°C/W

Marking (Note 5)



Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: (a) Device mounted on a glass-epoxy board (a) (b) Device mounted on a glass-epoxy board (b)

Note 3: V_{DD} = 24 V, T_{ch} = 25°C (initial), L = 0.2 mH, I_{AR} = 13 A

Note 4: Repetitive rating: pulse width limited by max channel temperature

Note 5: • on the lower left of the marking indicates Pin 1.

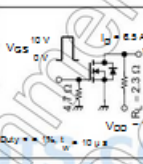
* Weekly code: (Three digits)

Week of manufacture
(01 for first week of year, continuing up to 52 or 53)
Year of manufacture
(The last digit of the calendar year)

Note 6: A line under a Lot No. identifies the indication of product Labels.
Not underlined: [[Pb]]/INCLUDES > MCV
Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product. The RoHS is the Directive 2002/95/EC of the European Parliament and of the Council of 27 January 2003 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I_{GSS}	V_{GS} = ± 20 V, V_{DS} = 0 V	□	□	± 100	nA
Drain cut-OFF current		I_{DSS}	V_{DS} = 30 V, V_{GS} = 0 V	□	□	10	μA
Drain-source breakdown voltage		$V_{(BR)\ DSS}$	I_D = 10 mA, V_{GS} = 0 V	30	□	□	V
		$V_{(BR)\ DSX}$	I_D = 10 mA, V_{GS} = − 20 V	10	□	□	
Gate threshold voltage		V_{th}	V_{DS} = 10 V, I_D = 1 mA	1.3	□	2.5	V
Drain-source ON resistance		$R_{DS\ (ON)}$	V_{GS} = 4.5 V, I_D = 6.5 A	□	7.5	10	mΩ
			V_{GS} = 10 V, I_D = 6.5 A	□	5.1	6.6	
Forward transfer admittance		$\|Y_{fs}\|$	V_{DS} = 10 V, I_D = 6.5 A	15	30	□	S
Input capacitance		C_{iss}	V_{DS} = 10 V, V_{GS} = 0 V, f = 1 MHz	□	1800	□	pF
Reverse transfer capacitance		C_{rss}		□	370	□	
Output capacitance		C_{oss}		□	570	□	
Switching time	Rise time	t_r		□	15	□	ns
	Turn-ON time	t_{on}		□	28	□	
	Fall time	t_f		□	21	□	
	Turn-OFF time	t_{off}		□	54	□	
Total gate charge (gate-source plus gate-drain)		Q_g	V_{DD} ≈ − 24 V, V_{GS} = 10 V, I_D = 13 A	□	42	□	nC
Gate-source charge 1		Q_{gs1}		□	6.5	□	
Gate-drain ("miller") charge		Q_{gd}		□	14	□	

Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Drain reverse current	Pulse (Note 1)	I_{DRP}	□	□	□	52	A
Forward voltage (diode)		V_{DSF}	I_{DR} = 13 A, V_{GS} = 0 V	□	□	− 1.2	V